HCC/HCF4095B HCC/HCF4096B

GATE J-K MASTER-SLAVE FLIP-FLOPS

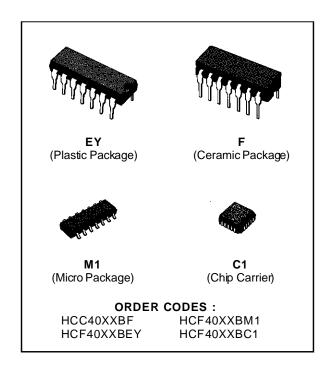
- 16 MHz TOGGLE RATE (typ.) AT Vpp - Vss = 10V
- **■** GATED INPUTS
- QUIESCENT CURRENT SPECIFIED TO 20v FOR HCC DEVICE
- 5V, 10V AND 15V PARAMETRIC RATINGS
- INPUT CURRENT OF 100 nA AT 18V AND 25oC FOR HCC DEVICE
- 100% TESTED FOR QUIESCENT CURRENT
- MEETS ALL REQUIREMENTS OF JEDECTEN-TATIVE STANDARD No 13 A, "STANDARD SPECIFICATIONS FOR DESCRIPTION OF B SERIES CMOS DEVICES"

DESCRIPTION

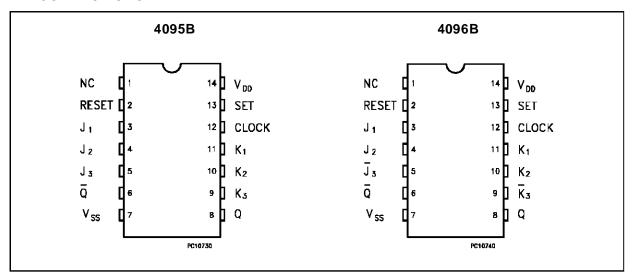
The **HCC4095B/4096B** (extended temperature range) and **HCF4095B/4096B** (intermediate temperature range) are monolithic integrated circuits, available in 14 lead dual in-line plastic or ceramic package and plastic micropackage.

The **HCC/HCF4095B** and **HCC/HCF4096B** are J-K Master-Slave Flip-Flops featuring separate AND gating of multiple J and Kinputs. The gated J-Kinput control transfer of information into the master section during clocked operation. Information on the J-K

inputs is transferred to the Q and \overline{Q} outputs on the positive edge of the clock pulse. SET and RESET inputs (active high) are provided for asynchronous operation.

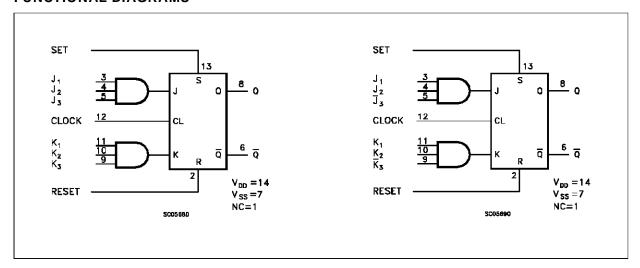


PIN CONNECTIONS

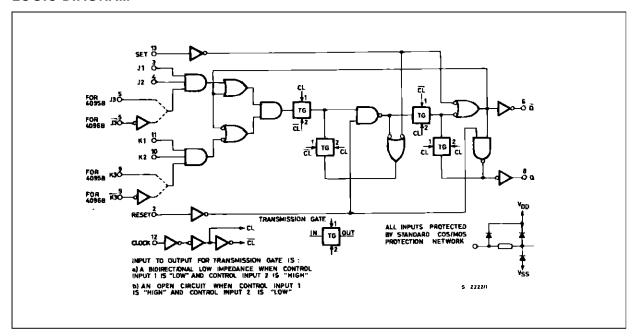


September 1988 1/13

FUNCTIONAL DIAGRAMS



LOGIC DIAGRAM



TRUTH TABLES

SYNCHRONOUS OPERATION (S=0 R=0)

	ore Positive ransition	Outputs After Positive Clock Transition		
J *	K *	Q	Q	
0	0	No Change		
0	1	0	1	
1	0	1 0		
1	1	Toggles		

ASYNCHRONOUS OPERATION (J and K DON'T CARE)

S	R	Q	Q
0	0	No CI	hange
0	1	0	1
1	0	1	0
1	1	0	0

 $^{0 =} V_{SS}, 1 = V_{DD}$



^{*} For 4095B J = J1 • J2 • <u>J3</u>, K = K1 • K2 • <u>K3</u> * For 4095B J = J1 • J2 • <u>J3</u>, K = K1 • K2 • <u>K3</u>

ABSOLUTE MAXIMUM RATING

Symbol	Parameter	Value	Unit
V _{DD} *	Supply Voltage: HCC Types HCF Types	-0.5 to +20 -0.5 to +18	V
Vi	Input Voltage	-0.5 to V _{DD} + 0.5	V
II	DC Input Current (any one input)	± 10	mA
P _{tot}	Total Power Dissipation (per package) Dissipation per Output Transistor	200	mW
	for Top = Full Package Temperature Range	100	mW
T _{op}	Operating Temperature: HCC Types HCF Types	-55 to +125 -40 to +85	°C °C
T _{stg}	Storage Temperature	-65 to +150	°C

Stresses above those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. This is a stress rating only and functional operation of the device at these or any other conditions above those indicated in the operational sections of this specification is not implied. Exposure to absolute maximum rating conditions for external periods may affect device reliability.

RECOMMENDED OPERATING CONDITIONS

Symbol	Parameter	Value	Unit
V_{DD}	Supply Voltage: HCC Types	3 to 18	V
	HCF Types	3 to 15	V
V_{I}	Input Voltage	0 to V _{DD}	V
Top	Operating Temperature: HCC Types	-55 to +125	°C
	HCF Types	-40 to +85	°C

^{*} All voltage values are referred to V_{SS} pin voltage.

STATIC ELECTRICAL CHARACTERISTICS (over recommended operating conditions)

				Test Con	ditios		Value							
Symbol	Parame	ter	(V)	Vo	lo	V _{DD}	TLO	w *		25 °C		Тню	эн *	Unit
				(V)	(μA)	(V)	Min.	Max.	Min.	Тур.	Max.	Min.	Max.	
ΙL	Quiescent		0/5			5		1		0.02	1		30	
	Current	HCC	0/10			10		2		0.02	2		60	
		Types	0/15			15		4		0.02	4		120	^
			0/20			20		20		0.04	20		600	μΑ
		HCF	0/5			5		4		0.02	4		30	
		Types	0/10			10		8		0.02	8		60	
		1,700	0/15			15		16		0.02	16		120	
VoH	Output High	•	0/5		< 1	5	4.95		4.95			4.95		
	Voltage		0/10		< 1	10	9.95		9.95			9.95		V
			0/15		< 1	15	14.95		14.95			14.95		
Vol	Output Low		5/0		< 1	5		0.05			0.05		0.05	
	Voltage		10/0		< 1	10		0.05			0.05		0.05	V
			15/0		< 1	15		0.05			0.05		0.05	
V _{IH}	Input High			4.5	< 1	5	3.5		3.5			3.5		
	Voltage			9	< 1	10	7		7			7		V
				13.5	< 1	15	11		11			11		
V _{IL}	Input Low			0.5	< 1	5		1.5			1.5		1.5	
	Voltage			1	< 1	10		3			3		3	V
				1.5	< 1	15		4			4		4	
Іон	Output		0/5	2.5		5	-2		-1.6	-3.2		-1.15		
	Drive	HCC	0/5	4.6		5	-0.64		-0.51	-1		-0.36		
	Current	Types	0/10	9.5		10	-1.6		-1.3	-2.6		-0.9		
			0/15	13.5		15	-4.2		-3.4	-6.8		-2.4		mA
			0/5	2.5		5	-1.53		-1.36	-3.2		-1.1		
		HCF	0/5	4.6		5	-0.52		-0.44	-1		-0.36		
		Types	0/10	9.5		10	-1.3		-1.1	-2.6		-0.9		
			0/15	13.5		15	-3.6		-3.0	-6.8		-2.4		
loL	Output	нсс	0/5	0.4		5	0.64		0.51	1		0.36		
	Sink	Types	0/10	0.5		10	1.6		1.3	2.6		0.9		
Curre	Current	Types	0/15	1.5		15	4.2		3.4	6.8		2.4		mA
		HCF	0/5	0.4		5	0.52		0.44	1		0.36		
		Types	0/10	0.5		10	1.3		1.1	2.6		0.9		
		1,7003	0/15	1.5		15	3.6		3.0	6.8		2.4		
I _{IH} , I _{IL}	Input Leaka	ge	0/18	- ا برم	nut	18		±0.1		±10 ⁻⁵	±0.1		±1	^
	Current	-	0/15	Any In	put	15		±0.3		±10 ⁻⁵	±0.3		±1	μΑ
Cı	Input Capac	itance		Any In	put					5	7.5			pF

^{*} T_{LOW} = -55 °C for **HCC** device: -40 °C for **HCF** device.

The Noise Margin for both "1" and "0" level is: 1V min. with V_{DD} = 5 V, 2 V min. with V_{DD} = 10 V, 2.5 V min. with V_{DD} = 15 V

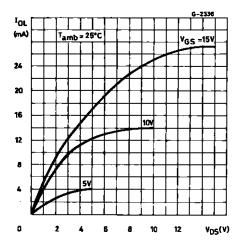


^{*} T_{HIGH} = +125 °C for **HCC** device: +85 °C for **HCF** device.

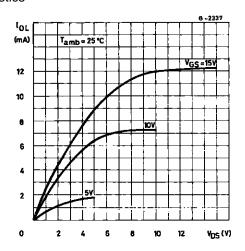
DYNAMIC ELECTRICAL CHARACTERISTICS ($T_{amb} = 25$ °C, $C_L = 50$ pF, $R_L = 200$ K Ω , typical temperature coefficent for all V_{DD} values is 03 %/°C, all input rise and fall times= 20 ns)

Symbol	Parameter	Test Conditions		Value			
Syllibol		V _{DD} (V) Min.	Тур.	Max.	Unit	
tplH	Propagation Delay Time	5		250	500		
t _{PHL}		10		100	200	ns	
		15		75	150		
tplH	Propagation Delay Time	5		150	300		
t _{PHL}	(Set or Reset)	10		75	150	ns	
		15		50	100		
t _{THL}	Transition Time	5		100	200		
t_{TLH}		10		50	100	ns	
		15		40	80		
f _{CL}	Maximum Clock Input Frequency	5	3.5	7			
		10	8	16		MHz	
		15	12	24			
t _W	Clock Pulse Width	5	140	70			
		10	60	30		ns	
		15	40	20			
t _r t _f	Clock Input Rise or Fall Time	5			15		
		10			5	μs	
		15			5		
tw	Set or Reset Pulse Width	5	200	100			
		10	100	50		ns	
		15	50	25			
t _{setup}	Data Setup Time	5	400	200			
		10	160	80		ns	
		15	100	50			

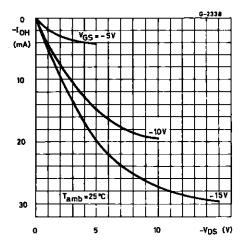
Typical Output Low (sink) Current Characteristics



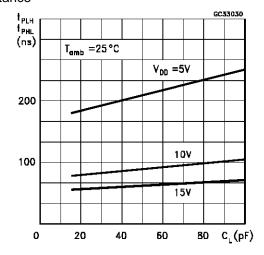
Minimum Output low (sink) Current Characteristics



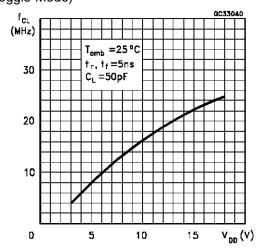
Typical Output High (source) Current Characteristics



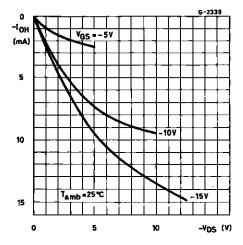
Typical Propagation Delay Time vs Load Capacitance



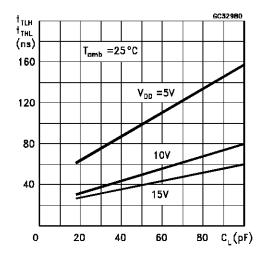
Typical Clock Frequency vs Supply Voltage (Toggle Mode)



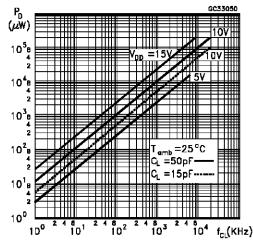
Minimum Output High (source) Current Characteristics



Typical Transition Time vs Load Capacitance

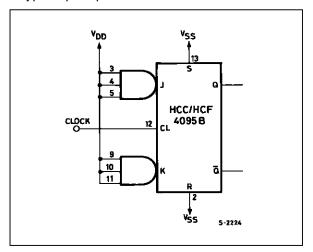


Typical Power Power Dissipation Vs. Input Clock Frequency

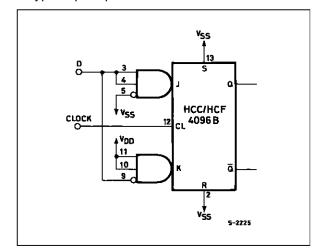


TYPICAL APPLICATIONS

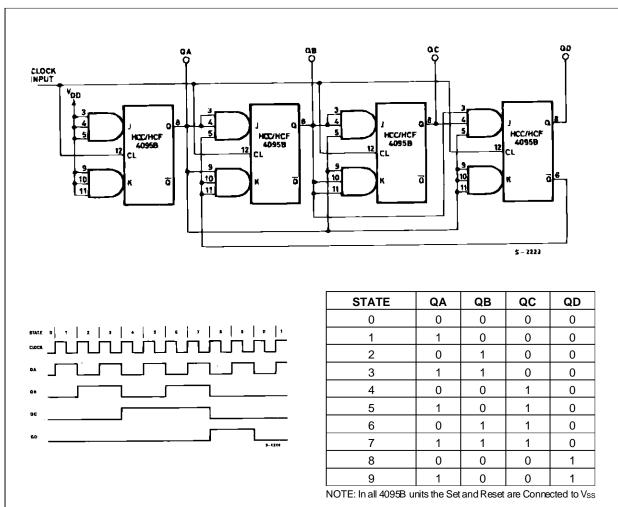
T-type Flip-Flop



D-type Flip-Flop

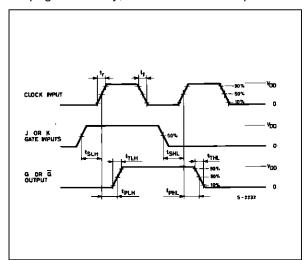


Synchronous Binary Divide by Ten Counter

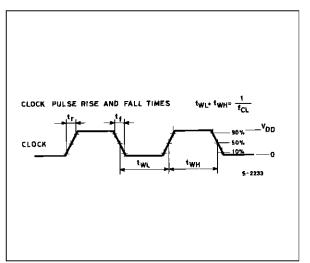


WAVEFORMS

Propagation Delay, Transition and Setup Time

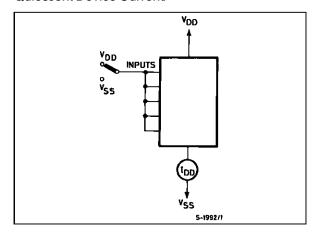


Clock Pulse Rise and Fall Time

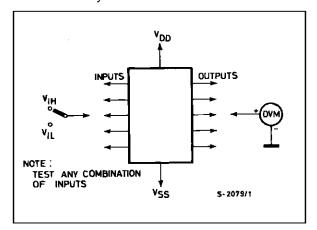


TEST CIRCUITS

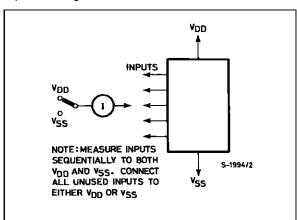
Quiescent Device Current.



Noise Immunity.



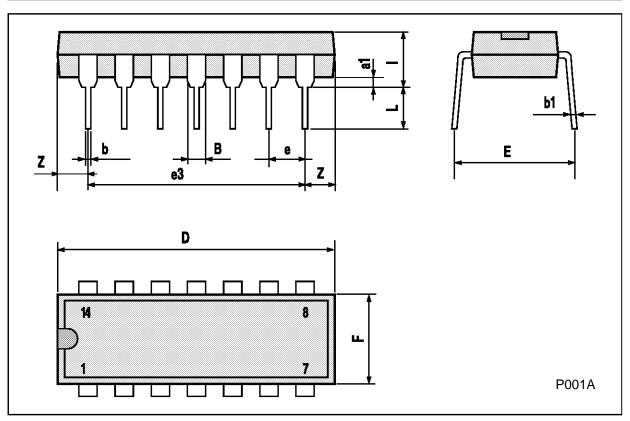
Input Leakage Current.





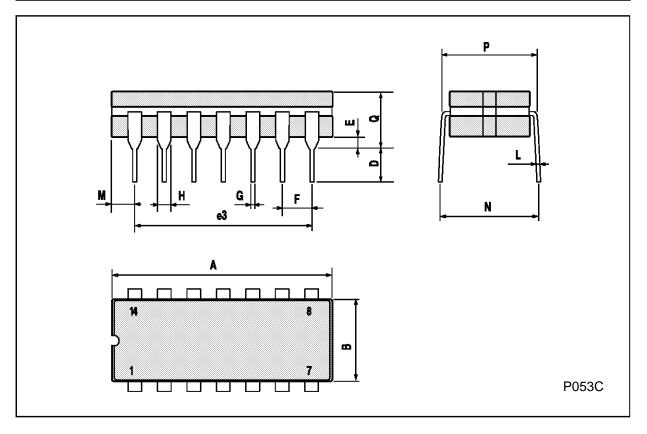
Plastic DIP14 MECHANICAL DATA

DIM.		mm			inch			
	MIN.	TYP.	MAX.	MIN.	TYP.	MAX.		
a1	0.51			0.020				
В	1.39		1.65	0.055		0.065		
b		0.5			0.020			
b1		0.25			0.010			
D			20			0.787		
E		8.5			0.335			
е		2.54			0.100			
e3		15.24			0.600			
F			7.1			0.280		
I			5.1			0.201		
L		3.3			0.130			
Z	1.27		2.54	0.050		0.100		



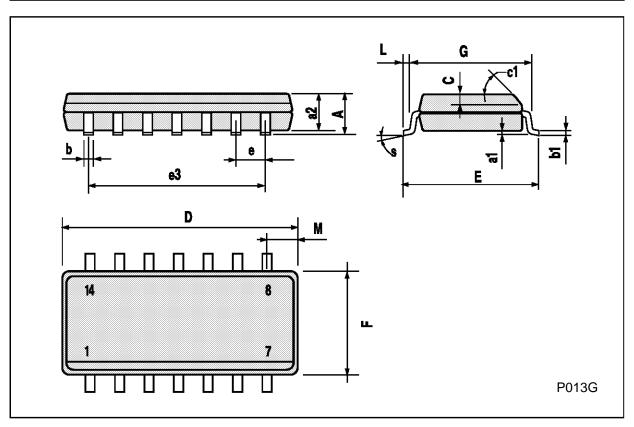
Ceramic DIP14/1 MECHANICAL DATA

DIM.		mm		inch				
J	MIN.	TYP.	MAX.	MIN.	TYP.	MAX.		
Α			20			0.787		
В			7.0			0.276		
D		3.3			0.130			
E	0.38			0.015				
e3		15.24			0.600			
F	2.29		2.79	0.090		0.110		
G	0.4		0.55	0.016		0.022		
Н	1.17		1.52	0.046		0.060		
L	0.22		0.31	0.009		0.012		
М	1.52		2.54	0.060		0.100		
N			10.3			0.406		
Р	7.8		8.05	0.307		0.317		
Q			5.08			0.200		



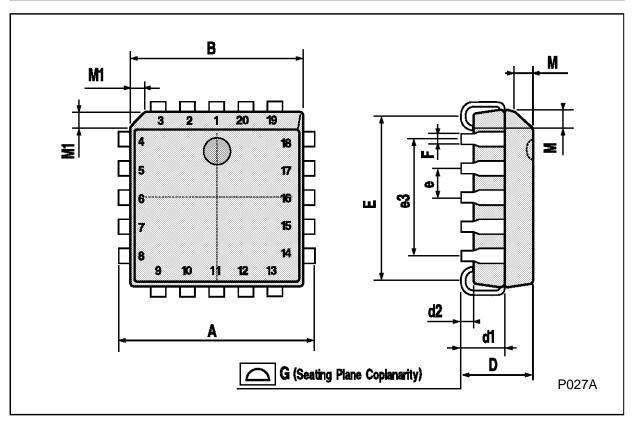
SO14 MECHANICAL DATA

DIM.		mm			inch				
Dilvi.	MIN.	TYP.	MAX.	MIN.	TYP.	MAX.			
Α			1.75			0.068			
a1	0.1		0.2	0.003		0.007			
a2			1.65			0.064			
b	0.35		0.46	0.013		0.018			
b1	0.19		0.25	0.007		0.010			
С		0.5			0.019				
c1			45°	(typ.)					
D	8.55		8.75	0.336		0.344			
Е	5.8		6.2	0.228		0.244			
е		1.27			0.050				
e3		7.62			0.300				
F	3.8		4.0	0.149		0.157			
G	4.6		5.3	0.181		0.208			
L	0.5		1.27	0.019		0.050			
М			0.68			0.026			
S			8° (ı	max.)					



PLCC20 MECHANICAL DATA

DIM.		mm		inch			
5	MIN.	TYP.	MAX.	MIN.	TYP.	MAX.	
А	9.78		10.03	0.385		0.395	
В	8.89		9.04	0.350		0.356	
D	4.2		4.57	0.165		0.180	
d1		2.54			0.100		
d2		0.56			0.022		
E	7.37		8.38	0.290		0.330	
е		1.27			0.050		
e3		5.08			0.200		
F		0.38			0.015		
G			0.101			0.004	
М		1.27			0.050		
M1		1.14			0.045		



Information furnished is believed to be accurate and reliable. However, SGS-THOMSON Microelectronics assumes no responsability for the consequences of use of such information nor for any infringement of patents or other rights of third parties which may results from its use. No license is granted by implication or otherwise under any patent or patent rights of SGS-THOMSON Microelectronics. Specifications mentioned in this publication are subject to change without notice. This publication supersedes and replaces all information previously supplied. SGS-THOMSON Microelectronics products are not authorized for use as critical components in life support devices or systems without express written approval of SGS-THOMSON Microelectonics.

© 1994 SGS-THOMSON Microelectronics - All Rights Reserved

SGS-THOMSON Microelectronics GROUP OF COMPANIES

Australia - Brazil - France - Germany - Hong Kong - Italy - Japan - Korea - Malaysia - Malta - Morocco - The Netherlands - Singapore - Spain - Sweden - Switzerland - Taiwan - Thailand - United Kingdom - U.S.A

